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#51/Amend E
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Thomas A. Figura, Kevin Donohoe, & Thomas Dunbar

Serial No.: 09/471,460

Filed: December 22, 1999

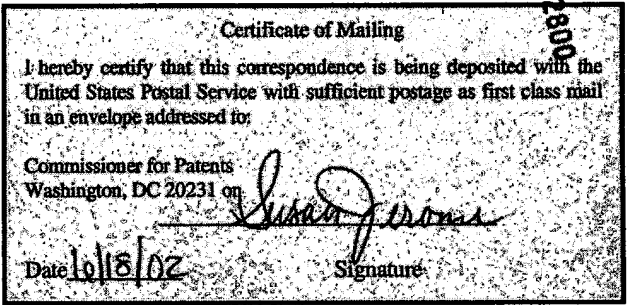
Title: USE OF A PLASMA SOURCE TO FORM A LAYER
DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

§
§ Group Art Unit: 2825
§
§ Application Examiner: Calvin Lee
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§ Atty. Docket: 94-0280.03
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AMENDMENT AND RESPONSE TO THE
OFFICE ACTION DATED MARCH 20, 2002

Commissioner for Patents
Washington, D.C. 20231



Dear Sir:

Applicants submit this Amendment and Response to the Office Action dated March 20, 2002. Please amend the above-captioned application as follows.

IN THE CLAIMS

Please amend the claims to the form described below.

45. (Thrice amended) A method of providing a material in a site between metal features on a wafer, comprising:

- performing a deposition of said material over said wafer in said site;
- and
- etching said material in the same general site used to perform said deposition, wherein said step of etching further comprises etching generally simultaneously with performing said deposition.

El